

Al₂O₃ SPUTTERING TARGET AND PRODUCTION METHOD THEREOF

ABSTRACT

5

An Al₂O₃ sputtering target having a purity of 99.99 wt% or higher, a relative density of 85% or higher and 95% or less, a volume resistivity of $10 \times 10^{14} \Omega \cdot \text{cm}$ or less, and a dielectric tangent of 15×10^{-4} or more. An object of the present invention is to provide an Al₂O₃ sputtering target having favorable sputtering characteristics, and in particular an Al₂O₃ sputtering target and a production method thereof capable of increasing the deposition rate without having to increase the sputtering power.

10